Method of Plasma Etching with Pattern Mask

ABSTRACT OF THE INVENTION

The present invention provides a method of plasma etching with pattern mask. There are two different devices in the two section of a wafer, comprising silicon and Gallium Arsenide (GaAs). The Silicon section is for general semiconductor. And the GaAs section is for RF device. The material of pad in the silicon is usually metal, and metal oxide is usually formed on the pads. The metal oxide is unwanted for further process; therefore it should be removed by plasma etching process. A film is attached to the surface of the substrate exposing the area need for etching. Then a mask is attached and aligned onto the film therefore exposing the area need for etching. Then plasma dry etching is applied on the substrate for removing the metal oxide.

Fig. 1A